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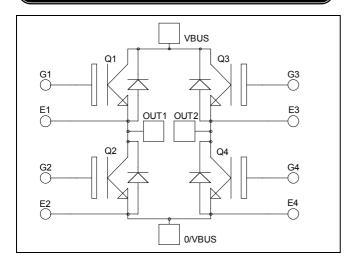


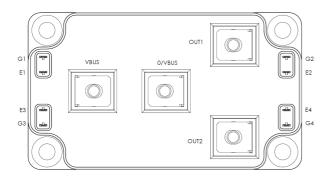






Full - Bridge Trench + Field Stop IGBT3 Power Module







Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
 - Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1700	V
T	Continuous Collector Current	$T_C = 25^{\circ}C$	250	
$I_{\rm C}$	Continuous Conector Current	$T_C = 80$ °C	150	A
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	300	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	890	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	300A @ 1600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$				350	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		2.0	2.4	V
$V_{CE(sat)}$	Conector Emitter Saturation Voltage	$I_{\rm C} = 150 {\rm A}$ $T_{\rm j} = 1$	$T_j = 125$ °C		2.4		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 3mA$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

Dynamic Characteristics

•	Characteristic	Test Conditions	Min	Тур	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		13.5		
C_{oes}	Output Capacitance	$V_{CE} = 25V$		0.55		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz		0.44		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		370		ns
T_{r}	Rise Time	$V_{GE} = 15V$		40		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 900V$ $I_{\text{C}} = 150A$		650		
T_{f}	Fall Time	$R_G = 4.7\Omega$		180		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		400		ns
T_{r}	Rise Time	$V_{GE} = 15V$		50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 900V$ $I_C = 150A$		800		
T_{f}	Fall Time	$R_G = 4.7\Omega$		300		
Eon	Turn-on Switching Energy	$V_{GE} = 15V \ V_{Bus} = 900V$ $T_j = 125^{\circ}C$		48		mJ
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$\begin{bmatrix} I_C = 150A \\ R_G = 4.7\Omega \end{bmatrix} T_j = 125^{\circ}C$		47		1117

Reverse diode ratings and characteristics

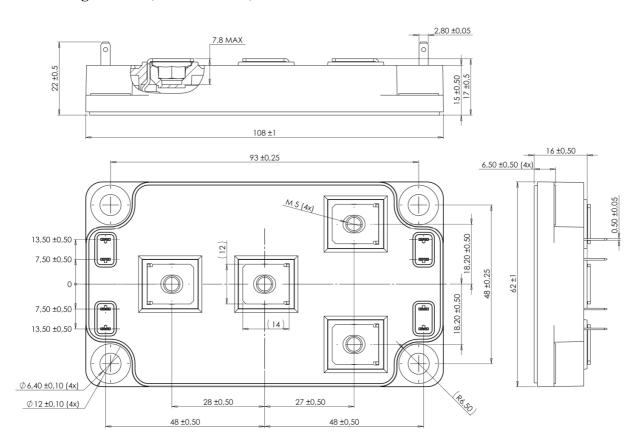
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1700			V
I_{RM}	Maximum Reverse Leakage Current	V _R =1700V	$T_j = 25^{\circ}C$			350	۸
1 _{RM}	Waximum Reverse Leakage Current		$T_{j} = 125^{\circ}C$			600	μA
I_F	DC Forward Current		$Tc = 80^{\circ}C$		150		Α
V_{F}	Diode Forward Voltage	$I_F = 150A$	$T_j = 25$ °C		1.8	2.2	V
▼ F	Blode Forward Voluge		$T_{i} = 125^{\circ}C$		1.9		,
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		385		ns
crr	reverse recovery Time	1.504	$T_j = 125$ °C		490		115
0	Payarsa Pagoyary Chargo	$I_F = 150A$ $V_R = 900V$	$T_j = 25^{\circ}C$		38		μС
Q_{rr}	Reverse Recovery Charge	$di/dt = 1600A/\mu s$	$T_{j} = 125^{\circ}C$		62		μС
$E_{\rm r}$	Payarga Pagayary Engray		$T_j = 25^{\circ}C$		17.5		mJ
\mathbf{r}_{r}	Reverse Recovery Energy		$T_j = 125$ °C		35		1113



Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
D	Junction to Case Thermal Resistance IGBT Diode				0.14	°C/W	
R_{thJC}			Diode			0.26	C/ W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range Storage Temperature Range			-40		150	
T_{STG}				-40		125	°C
T_{C}	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	11.111
Wt	Package Weight					300	g

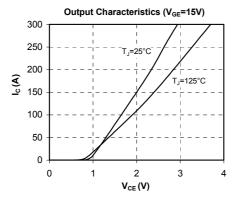
SP6 Package outline (dimensions in mm)

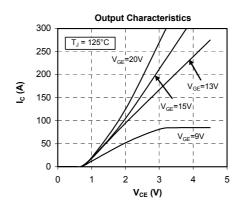


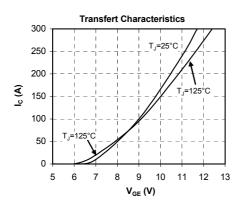
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

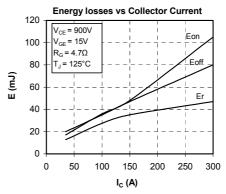


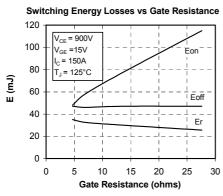
Typical Performance Curve

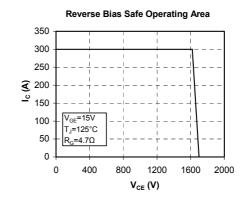


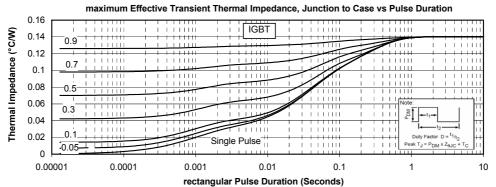






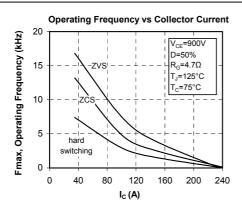


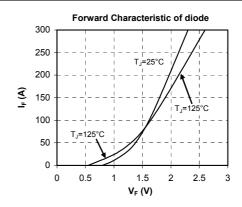


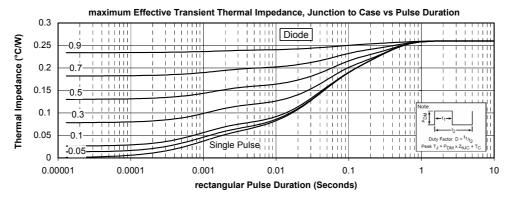


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